

IN THE CLAIMS:

Please cancel claim 20 without prejudice or disclaimer to the subject matter disclosed therein.

Claims 1-5 (Withdrawn)

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6. (Previously Amended) A method for fabricating a semiconductor device that includes an extended high-concentration dopant diffused layer of a first conductivity and a pocket dopant diffused layer of a second conductivity, comprising:

a first step of forming a gate electrode over a semiconductor region with a gate insulating film interposed therebetween;

a second step of implanting heavy ions into the semiconductor region on both sides of the gate electrode using the gate electrode as a mask, thereby forming a first ion implanted layer of the second conductivity, at least upper part of which is an amorphous layer;

a third step of implanting ions of a first dopant into the semiconductor region, in which the amorphous layer has been formed, using the gate electrode as a mask, thereby forming a second ion implanted layer of the first conductivity type; and

a fourth step of conducting a first annealing process to activate the first and second ion implanted layers, thereby forming the extended high-concentration dopant diffused layer of the first conductivity type through diffusion of the first dopant and the pocket dopant diffused layer of the second conductivity type, which is in contact with a bottom portion of the extended high-concentration dopant diffused layer, through diffusion of the heavy ions, respectively,

wherein the pocket dopant diffused layer includes, in a portion in contact with the extended high-concentration dopant diffused layer, a segregated part that has been formed through segregation of the heavy ions.

7. (Original) A method for fabricating a semiconductor device according to claim 6, wherein the segregated part of the pocket dopant diffused layer overlaps with a profile of the extended high-concentration dopant diffused layer.

8. (Previously Amended) A method for fabricating a semiconductor device according to claim 6, further comprising the steps of:

forming a sidewall spacer on side faces of the gate electrode after the third step has been performed;

implanting ions of a second dopant into the semiconductor region using the gate electrode and the sidewall spacer as a mask, thereby forming a third ion implanted layer of the first conductivity type; and

conducting a second annealing process to activate the third ion implanted layer, thereby forming a high-concentration dopant diffused layer of the first conductivity type, which is located outside of the extended high-concentration dopant diffused layer, has a junction deeper than that of the extended high-concentration dopant diffused layer and has been formed through diffusion of a second dopant.

9. (Previously Amended) A method for fabricating a semiconductor device according to claim 8, wherein the heavy ions are implanted at such an implant energy as forming an amorphous/crystalline interface, through implantation of the heavy ions, at a level equal to or deeper than a range of the first dopant and shallower than a range of the second dopant.

10. (Original) A method for fabricating a semiconductor device according to claim 6, further comprising the steps of:

implanting ions into a surface part of the semiconductor region, thereby forming a fourth ion implanted layer of a second conductivity type before the first step is performed; and

conducting a third annealing process to activate the fourth ion implanted layer, thereby forming a dopant diffused layer to be a channel region.

Claim 11 (Cancelled)

12. (Previously Amended) A method for fabricating a semiconductor device

according to claim 6, wherein the heavy ions are implanted at such an implant energy as making a range of the heavy ions equal to or deeper than a range of the first dopant and between one to three times as deep as the range of the first dopant.

13. (Original) A method for fabricating a semiconductor device according to claim 6, wherein the heavy ions are indium ions.

14. (Previously Amended) A method for fabricating a semiconductor device according to claim 13, wherein an implant dose of the indium ions is $5 \times 10^{13}/\text{cm}^2$ or more.

15. (Original) A method for fabricating a semiconductor device according to claim 6, wherein the first annealing process is a rapid thermal annealing process in which the semiconductor region is heated up to a temperature between 950°C and 1050°C at a rate between 100° per second and 150° per second and then kept at the temperature for a period of time between 1 second and 10 seconds.

Claims 16-20 (Cancelled)

21. (Original) A method for fabricating a semiconductor device according to claim 6, wherein the first dopant is arsenic.

22. (Original) A method for fabricating a semiconductor device according to claim 21, wherein the heavy ions are indium ions.

23. (Original) A method for fabricating a semiconductor device according to claim 8, wherein the heavy ions are indium ions, and the first dopant and the second dopant are arsenic.

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24. (Original) A method for fabricating a semiconductor device according to claim 10, wherein the fourth ion implanted layer is formed into the surface part of the semiconductor region by implanting indium ions.
